

# Masataka Hourai

## List of Publications by Year in descending order

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12  
papers

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#	ARTICLE	IF	CITATIONS
1	Oxygen concentration dependence of as-grown defect formation in nitrogen-doped Czochralski silicon single crystals. <i>Journal of Crystal Growth</i> , 2021, 570, 126236.	1.5	7
2	Recognition and Imaging of Point Defect Diffusion, Recombination, and Reaction During Growth of Czochralski-Silicon Crystals. <i>Journal of Electronic Materials</i> , 2020, 49, 5110-5119.	2.2	2
3	Oxygen Precipitation Properties of Nitrogen-Doped Czochralski Silicon Single Crystals with Low Oxygen Concentration. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900272.	1.8	9
4	Review and Comments for the Development of Point Defect-Controlled CZ-Si Crystals and Their Application to Future Power Devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800664.	1.8	14
5	Determination of Physical Properties for Point Defects during CZ Silicon Crystal Growth by High-Precision Thermal Simulations. <i>Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals</i> , 2011, 75, 657-664.	0.4	10
6	Defect Formation Behaviors in Heavily Doped Czochralski Silicon. <i>ECS Transactions</i> , 2006, 2, 95-107.	0.5	23
7	Dependence of Grown-in Defect Behavior on Oxygen Concentration in Czochralski Silicon Crystals. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 5725-5730.	1.5	16
8	Relationship between Grown-in Defects in Czochralski Silicon Crystals. <i>Japanese Journal of Applied Physics</i> , 1997, 36, L591-L594.	1.5	22
9	Formation of Grown-in Defects during Czochralski Silicon Crystal Growth. <i>Japanese Journal of Applied Physics</i> , 1997, 36, 6595-6600.	1.5	30
10	Observation of Ring-OSF Nuclei in CZ-Si Using Short-Time Annealing and Infrared Light Scattering Tomography. <i>Journal of the Electrochemical Society</i> , 1995, 142, 996-1001.	2.9	8
11	Formation Behavior of Infrared Light Scattering Defects in Silicon during Czochralski Crystal Growth. <i>Journal of the Electrochemical Society</i> , 1995, 142, 3193-3201.	2.9	27
12	Dependence of the Grown-in Defect Distribution on Growth Rates in Czochralski Silicon. <i>Japanese Journal of Applied Physics</i> , 1993, 32, 3675-3681.	1.5	132